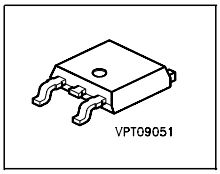
Cool MOS™ Power Transistor

V_{DS} @ T_{jmax}	560	V
$R_{DS(on)}$	0.6	Ω
I_D	7.6	A

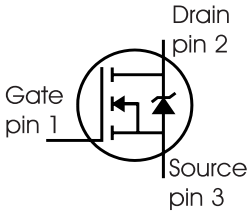
Feature

- New revolutionary high voltage technology
- Worldwide best $R_{DS(on)}$ in TO-252
- Ultra low gate charge
- Periodic avalanche rated
- Extreme d*v*/d*t* rated
- Ultra low effective capacitances
- Improved transconductance

P-TO252-3-1



Type	Package	Ordering Code	Marking
SPD08N50C3	P-TO252-3-1	Q67040-S4569	08N50C3



Maximum Ratings, at T_C = 25°C, unless otherwise specified

Parameter	Symbol	Value	Unit
Continuous drain current	I_D		A
T_C = 25 °C		7.6	
T_C = 100 °C		4.6	
Pulsed drain current, t_p limited by T_{jmax}	$I_{D\ puls}$	22.8	
Avalanche energy, single pulse	E_{AS}	230	mJ
I_D=5.5A, V_{DD}=50V			
Avalanche energy, repetitive t_{AR} limited by T_{jmax}[1)]	E_{AR}	0.5	
I_D=7.6A, V_{DD}=50V			
Avalanche current, repetitive t_{AR} limited by T_{jmax}	I_{AR}	7.6	A
Gate source voltage	V_{GS}	±20	V
Gate source voltage AC (f >1Hz)	V_{GS}	±30	
Power dissipation, T_C = 25°C	P_{tot}	83	W
Operating and storage temperature	T_j , T_{stg}	-55... +150	°C

Maximum Ratings

Parameter	Symbol	Value	Unit
Drain Source voltage slope V_{DS} = 400 V, I_D = 7.6 A, T_j = 125 °C	d*v*/d*t*	50	V/ns

Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Thermal resistance, junction - case	R_{thJC}	-	-	1.5	K/W
Thermal resistance, junction - ambient, leaded	R_{thJA}	-	-	75	
SMD version, device on PCB: @ min. footprint @ 6 cm^2 cooling area [2)]	R_{thJA}	 - -	 - -	 75 50	
Soldering temperature, 1.6 mm (0.063 in.) from case for 10s [3)]	T_{sold}	-	-	260	°C

Electrical Characteristics

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D=0.25mA	500	-	-	V
Drain-Source avalanche breakdown voltage	$V_{(BR)DS}$	V_{GS}=0V, I_D=7.6A	-	600	-	
Gate threshold voltage	$V_{GS(th)}$	I_D=350µA, V_{GS}=V_{DS}	2.1	3	3.9	
Zero gate voltage drain current	I_{DSS}	V_{DS}=500V, V_{GS}=0V, T_j=25°C, T_j=150°C	 - -	 0.5 -	 1 100	µA
Gate-source leakage current	I_{GSS}	V_{GS}=20V, V_{DS}=0V	-	-	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS}=10V, I_D=4.6A, T_j=25°C T_j=150°C	 - -	 0.5 1.5	 0.6 -	Ω
Gate input resistance	R_G	*f*=1MHz, open Drain	-	1.2	-	

Electrical Characteristics , at T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Transconductance	g_{fs}	$V_{DS}\geq 2*I_D*R_{DS(on)max}$, I_D=4.6A	-	6	-	S
Input capacitance	C_{iss}	V_{GS}=0V, V_{DS}=25V, f=1MHz	-	750	-	pF
Output capacitance	C_{oss}		-	350	-	
Reverse transfer capacitance	C_{rss}		-	12	-	
Effective output capacitance,[4] energy related	$C_{o(er)}$	V_{GS}=0V, V_{DS}=0V to 400V	-	56	-	pF
Effective output capacitance,[5] time related	$C_{o(tr)}$		-	30	-	
Turn-on delay time	$t_{d(on)}$	V_{DD}=400V, V_{GS}=0/10V, I_D=7.6A, R_G=12Ω	-	6	-	ns
Rise time	t_r		-	5	-	
Turn-off delay time	$t_{d(off)}$		-	60	-	
Fall time	t_f		-	7	-	

Gate Charge Characteristics

Gate to source charge	Q_{gs}	V_{DD}=400V, I_D=7.6A	-	3	-	nC
Gate to drain charge	Q_{gd}		-	17	-	
Gate charge total	Q_g	V_{DD}=400V, I_D=7.6A, V_{GS}=0 to 10V	-	32	-	
Gate plateau voltage	$V_{(plateau)}$	V_{DD}=400V, I_D=7.6A	-	5	-	V

[1] Repetitve avalanche causes additional power losses that can be calculated as $P_{AV}=E_{AR}*f$.

[2] Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70 µm thick) copper area for drain connection. PCB is vertical without blown air.

[3] Soldering temperature for TO-263: 220°C, reflow

[4] $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}.

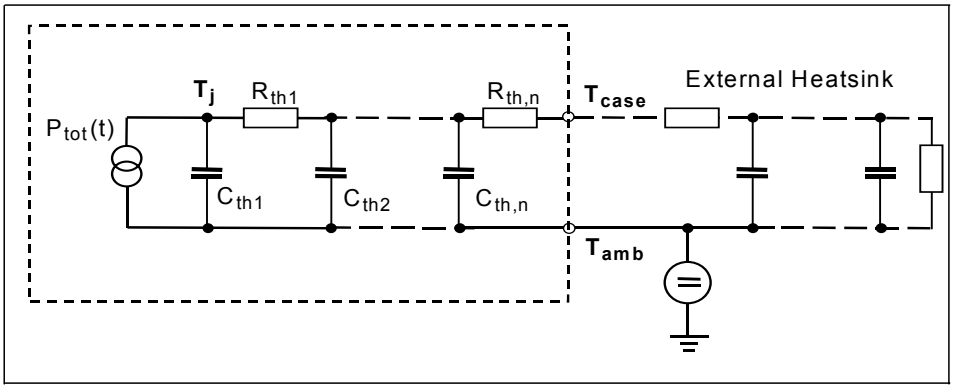
[5] $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}.

Electrical Characteristics, at T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Inverse diode continuous forward current	I_S	T_C=25°C	-	-	7.6	A
Inverse diode direct current, pulsed	I_{SM}		-	-	22.8	
Inverse diode forward voltage	V_{SD}	V_{GS}=0V, I_F=I_S	-	1	1.2	V
Reverse recovery time	t_{rr}	V_R=400V, I_F=I_S , di_F/dt=100A/µs	-	370	-	ns
Reverse recovery charge	Q_{rr}		-	3.6	-	µC
Peak reverse recovery current	I_{rrm}		-	25	-	A
Peak rate of fall of reverse recovery current	di_{rr}/dt		-	700	-	A/µs

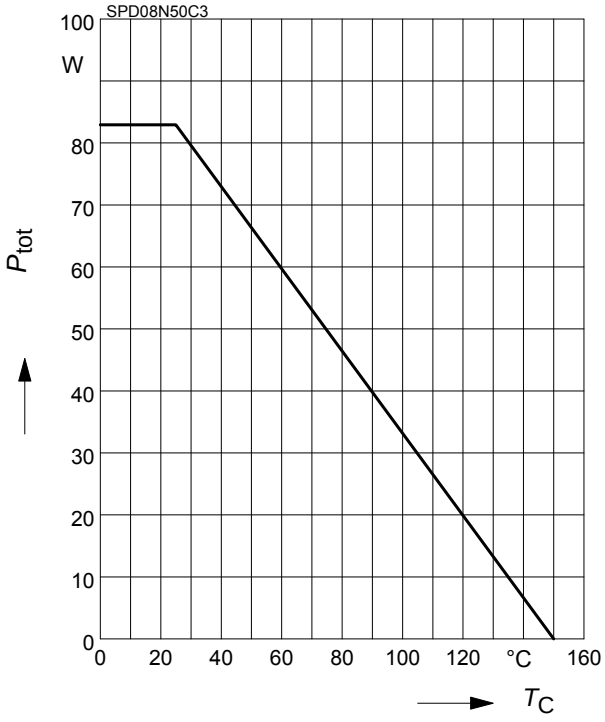
Typical Transient Thermal Characteristics

Symbol	Value	Unit	Symbol	Value	Unit
	typ.			typ.	
Thermal resistance			Thermal capacitance		
R_{th1}	0.024	K/W	C_{th1}	0.00012	Ws/K
R_{th2}	0.046		C_{th2}	0.0004578	
R_{th3}	0.085		C_{th3}	0.000645	
R_{th4}	0.308		C_{th4}	0.001867	
R_{th5}	0.317		C_{th5}	0.004795	
R_{th6}	0.112		C_{th6}	0.045	



1 Power dissipation

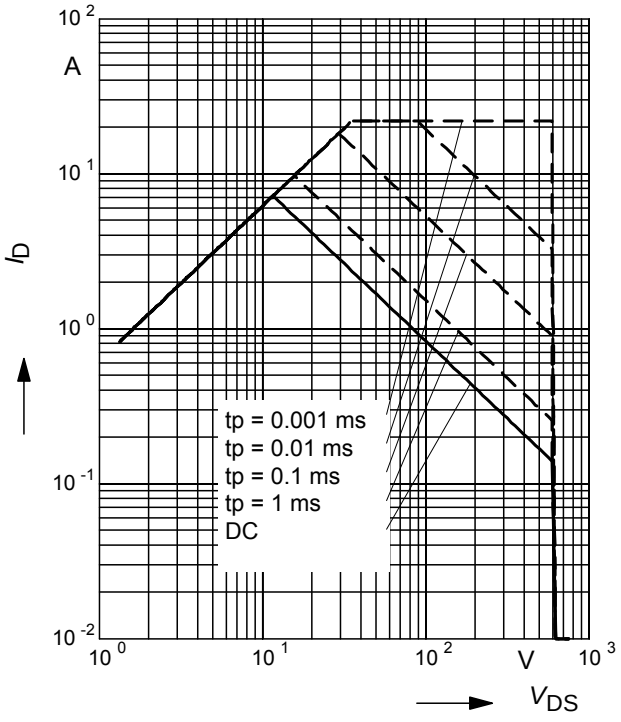
$P_{tot} = f(T_C)$



2 Safe operating area

$I_D = f(V_{DS})$

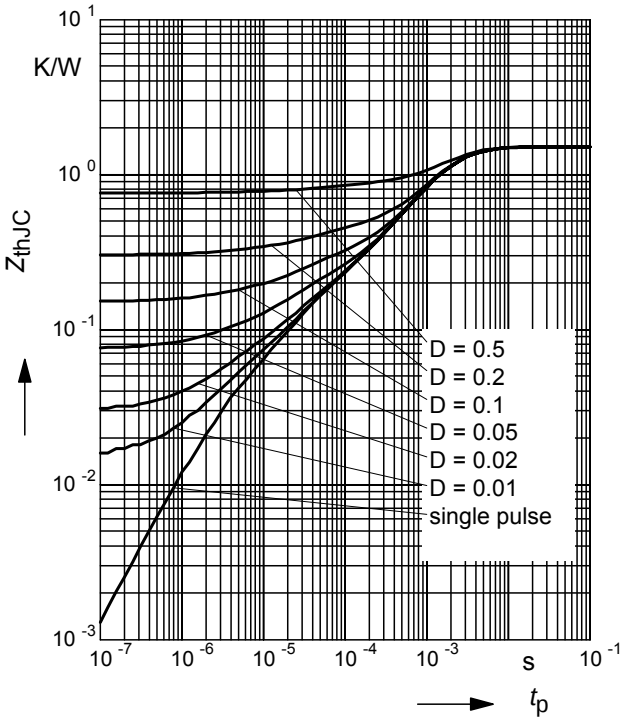
parameter : $D = 0$, T_C=25°C



3 Transient thermal impedance

$Z_{thJC} = f(t_p)$

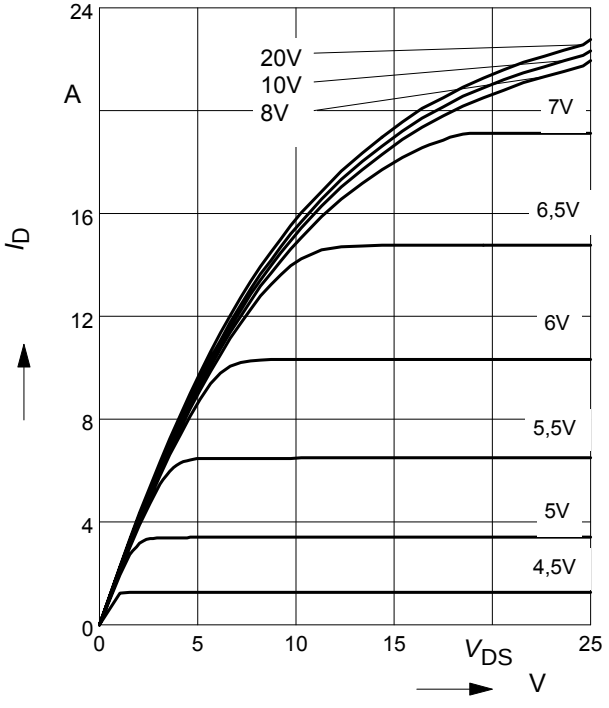
parameter: $D = t_p/T$



4 Typ. output characteristic

$I_D = f(V_{DS})$; T_j=25°C

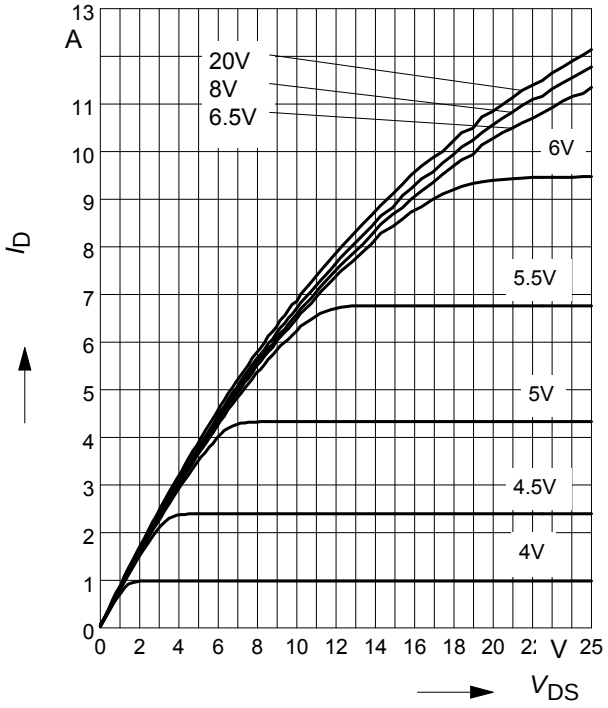
parameter: t_p = 10 µs, V_{GS}



5 Typ. output characteristic

$I_D = f(V_{DS})$; T_j=150°C

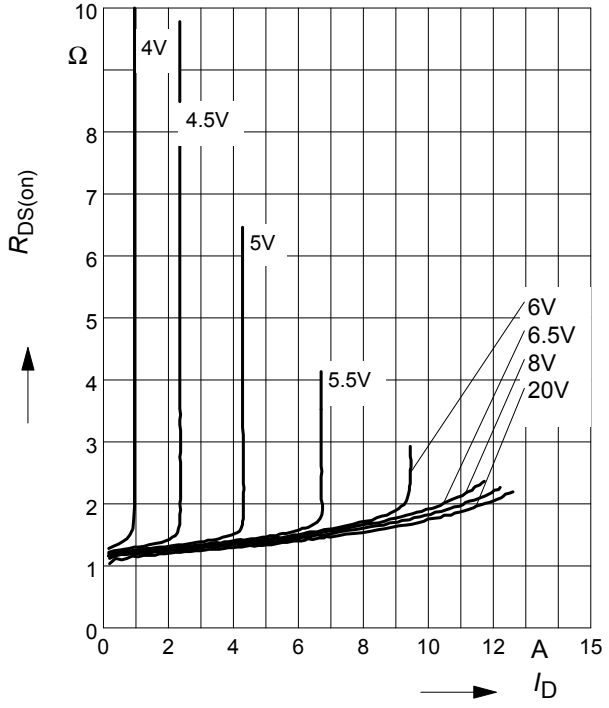
parameter: t_p = 10 µs, V_{GS}



6 Typ. drain-source on resistance

$R_{DS(on)}=f(I_D)$

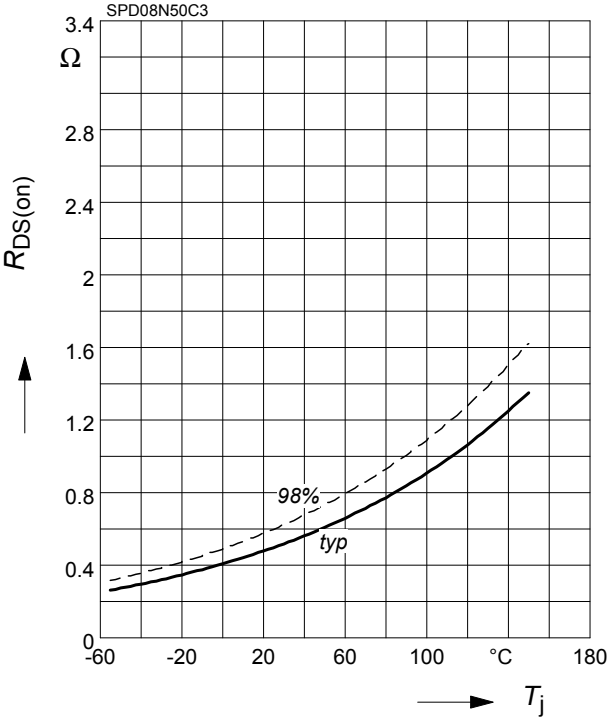
parameter: T_j=150°C, V_{GS}



7 Drain-source on-state resistance

$R_{DS(on)} = f(T_j)$

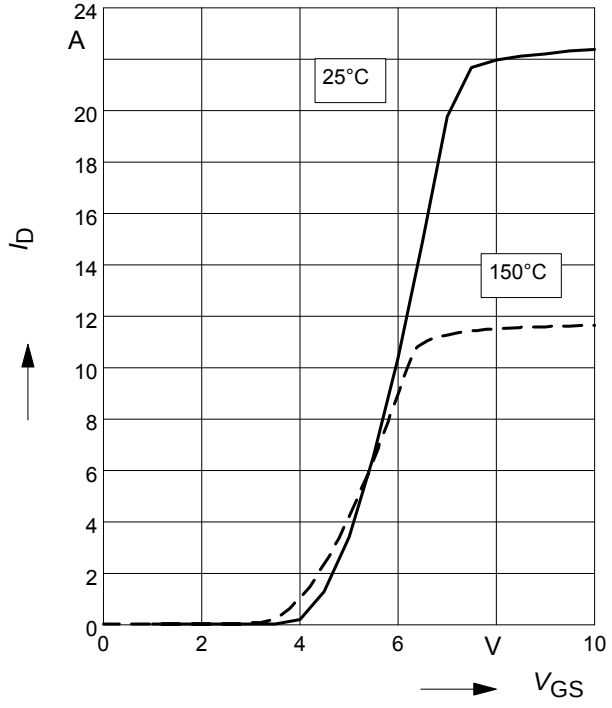
parameter : I_D = 4.6 A, V_{GS} = 10 V



8 Typ. transfer characteristics

$I_D= f(V_{GS})$; $V_{DS}\geq 2 \times I_D \times R_{DS(on)max}$

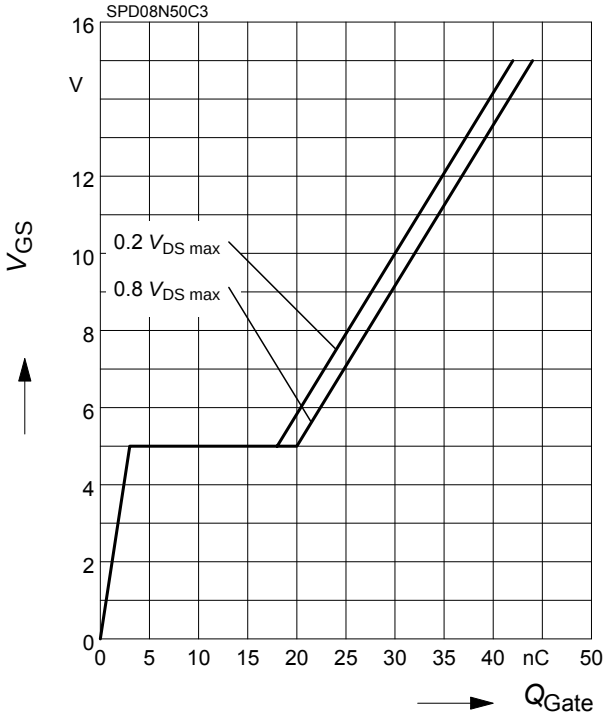
parameter: t_p = 10 µs



9 Typ. gate charge

$V_{GS} = f\ (Q_{Gate})$

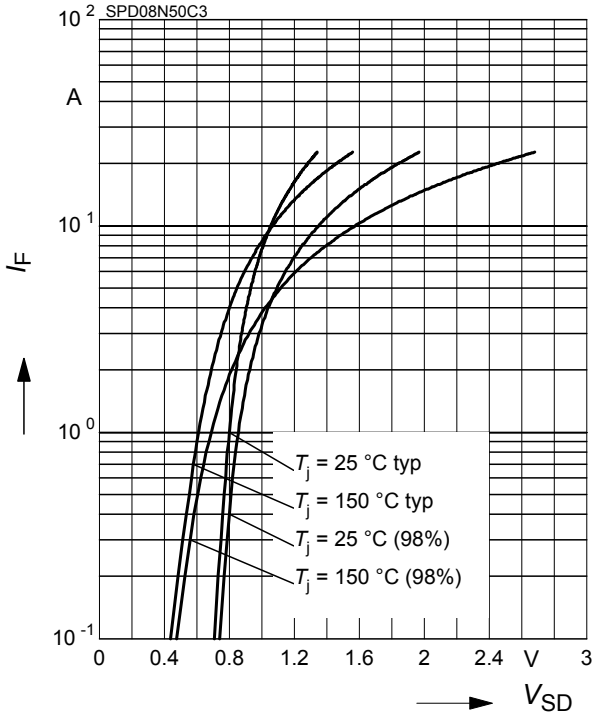
parameter: I_D = 7.6 A pulsed



10 Forward characteristics of body diode

$I_F = f\ (V_{SD})$

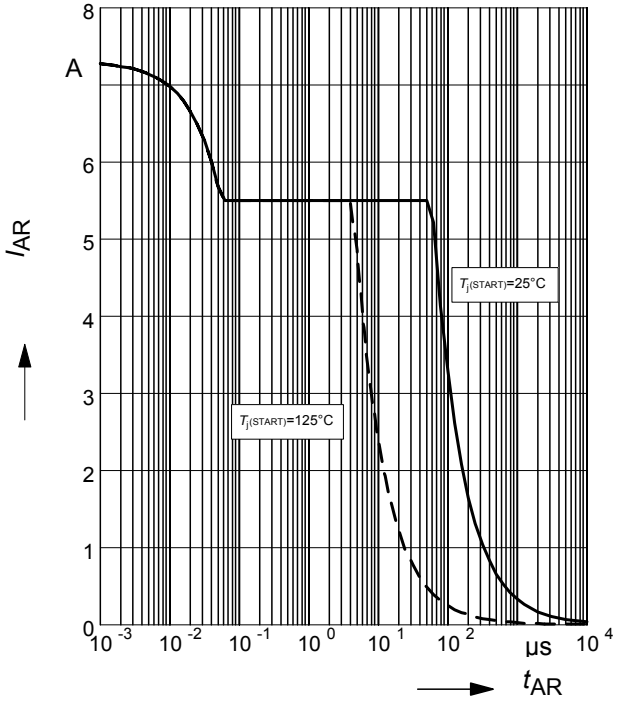
parameter: T_j , tp = 10 µs



11 Avalanche SOA

$I_{AR} = f\ (t_{AR})$

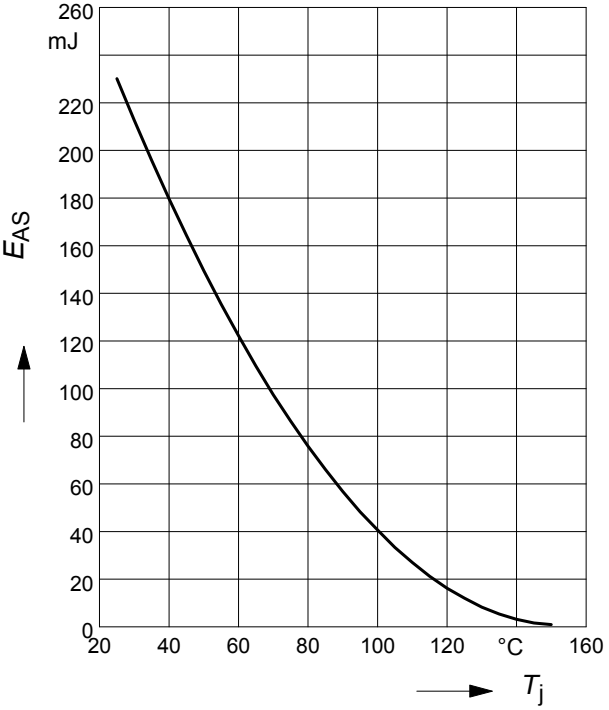
par.: $T_j \leq 150$ °C



12 Avalanche energy

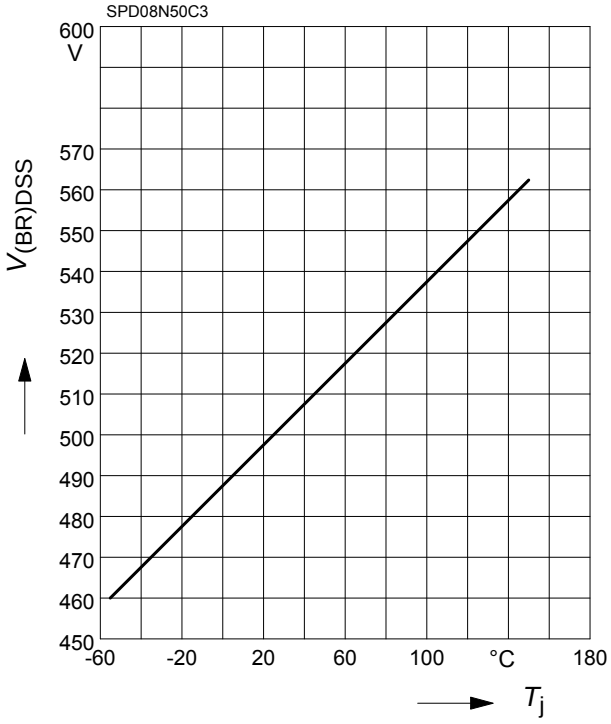
$E_{AS} = f\ (T_j)$

par.: I_D = 5.5 A, V_{DD} = 50 V



13 Drain-source breakdown voltage

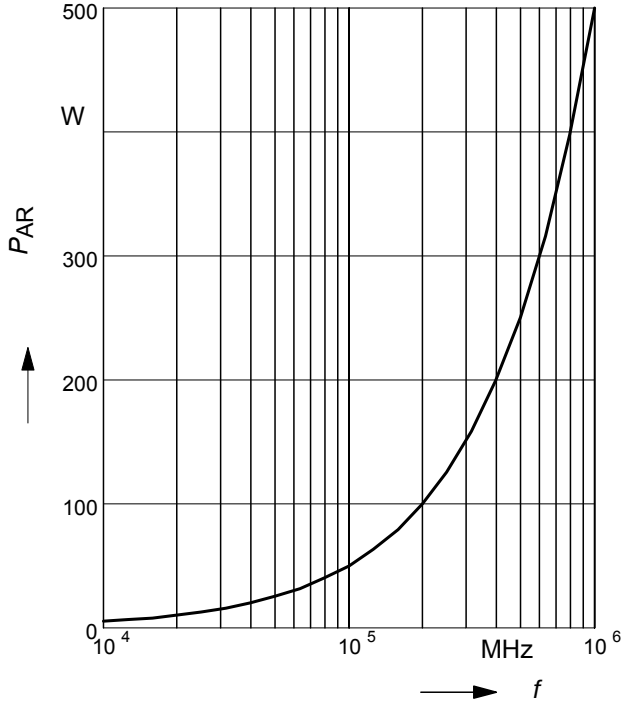
$V_{(BR)DSS} = f(T_j)$



14 Avalanche power losses

$P_{AR} = f(f)$

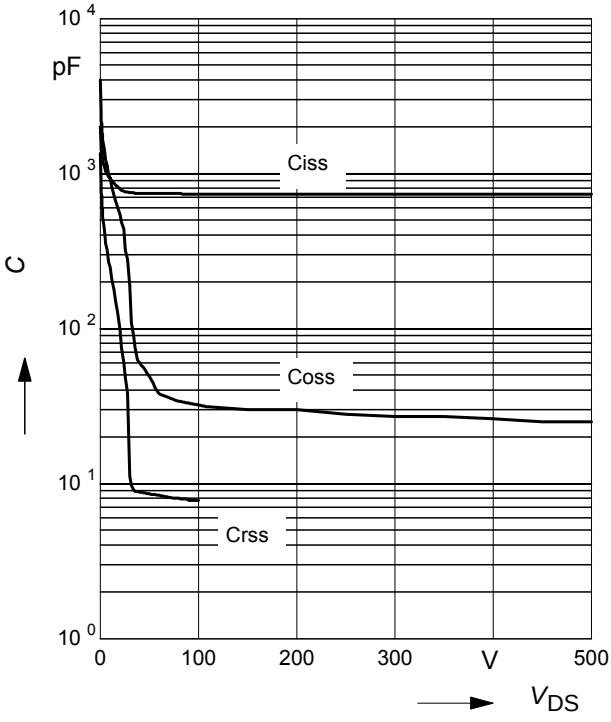
parameter: E_{AR}=0.5mJ



15 Typ. capacitances

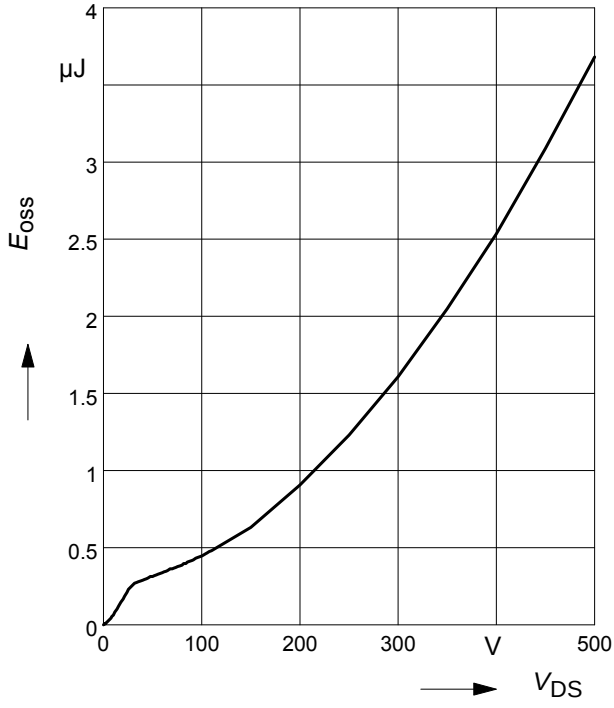
$C = f(V_{DS})$

parameter: V_{GS}=0V, f=1 MHz

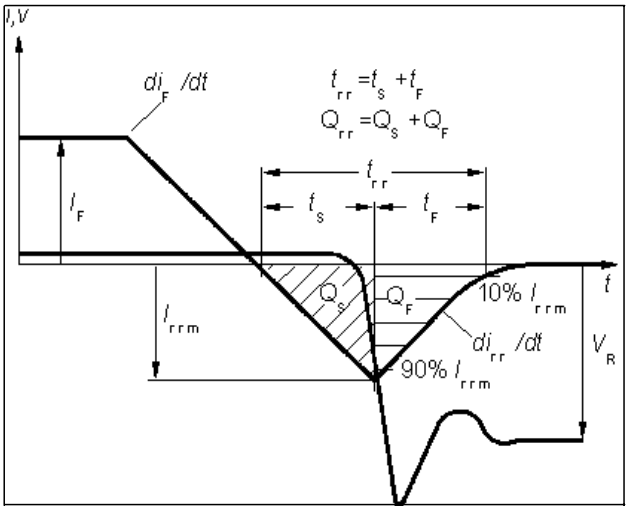


16 Typ. C_{oss} stored energy

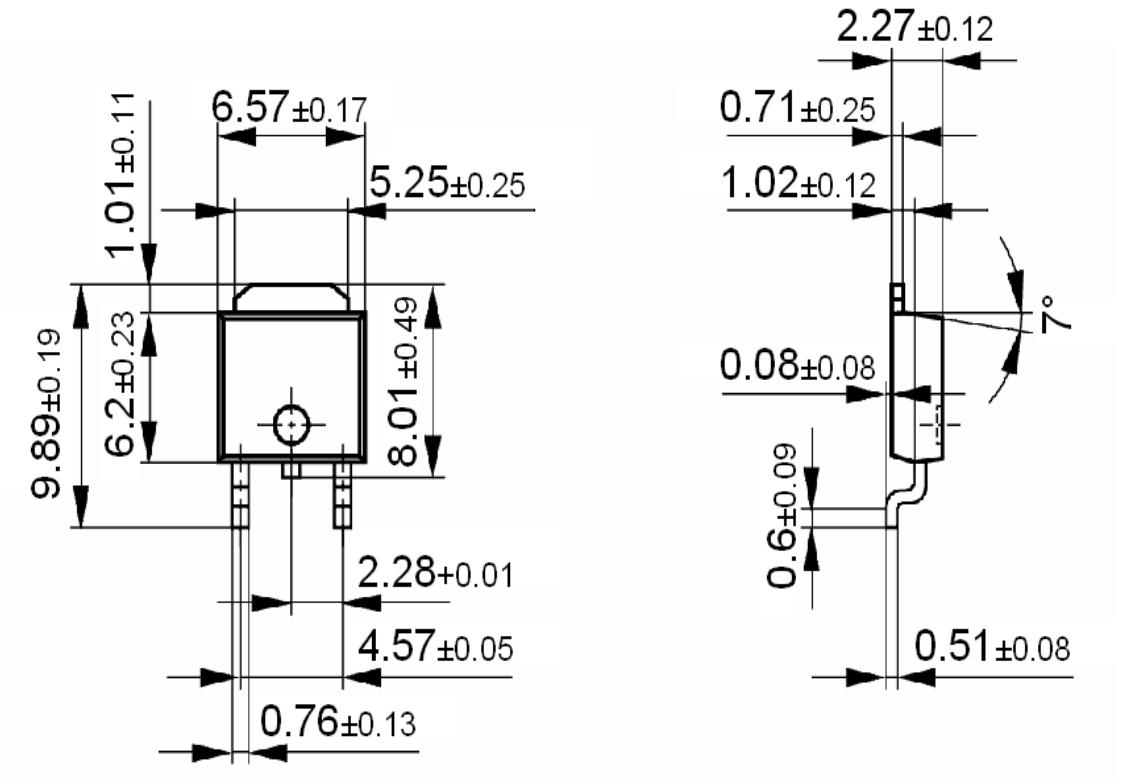
$E_{oss}=f(V_{DS})$



Definition of diodes switching characteristics



P-TO-252-3-1 (D-PAK)



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